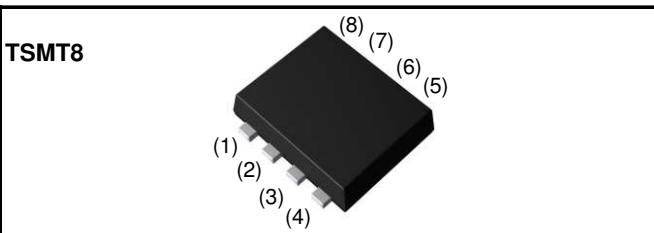


V_{DSS}	30V
$R_{DS(on)}$ (Max.)	54mΩ
I_D	3.5A
P_D	1.5W

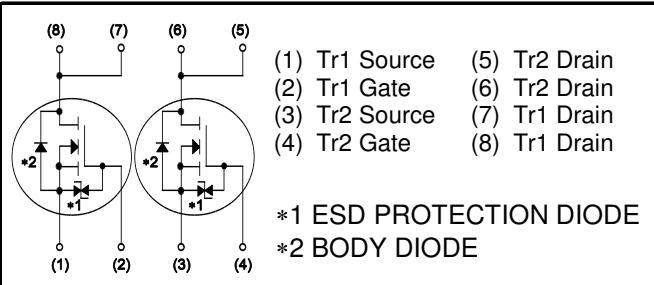
●Features

- 1) Low on - resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT8).
- 4) Pb-free lead plating ; RoHS compliant

●Outline



●Inner circuit



*1 ESD PROTECTION DIODE
*2 BODY DIODE

●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	180
	Tape width (mm)	8
	Basic ordering unit (pcs)	3,000
	Taping code	TR
	Marking	K02

●Absolute maximum ratings($T_a = 25^\circ\text{C}$) <It is the same ratings for the Tr1 and Tr2>

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	30	V
Continuous drain current	I_D * ¹	±3.5	A
Pulsed drain current	$I_{D,pulse}$ * ²	±12	A
Gate - Source voltage	V_{GSS}	±12	V
Power dissipation	P_D * ³	1.25	W / total
		0.9	W / element
	P_D * ⁴	0.6	W / total
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA} ^{*3}	-	-	83.3	°C/W
	R_{thJA} ^{*4}	-	-	227	°C/W

● Electrical characteristics ($T_a = 25^\circ\text{C}$) ,unless otherwise specified

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}$, $I_D = 1\text{mA}$	30	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D=1\text{mA}$ referenced to 25°C	-	30	-	mV/°C
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 12\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 10	μA
Gate threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = 10\text{V}$, $I_D = 1\text{mA}$	0.5	-	1.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)\text{th}}}{\Delta T_j}$	$I_D=1\text{mA}$ referenced to 25°C	-	-2.3	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}$ ^{*5}	$V_{GS}=4.5\text{V}$, $I_D=3.5\text{A}$	-	38	54	mΩ
		$V_{GS}=4.0\text{V}$, $I_D=3.5\text{A}$	-	40	56	
		$V_{GS}=2.5\text{V}$, $I_D=3.5\text{A}$	-	55	77	
		$V_{GS}=4.5\text{V}$, $I_D=3.5\text{A}$, $T_j=125^\circ\text{C}$	-	68	95	
Gate input resistannce	R_G	f = 1MHz, open drain	-	8	-	Ω
Transconductance	g_{fs} ^{*5}	$V_{DS}=10\text{V}$, $I_D=3.5\text{A}$	3	7	-	S

*1 Limited only by maximum temperature allowed.

*2 $P_w \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 Mounted on a ceramic board (30×30×0.8mm)

*4 Mounted on a FR4 (20×20×0.8mm)

*5 Pulsed

● **Electrical characteristics**($T_a = 25^\circ\text{C}$)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$ $V_{DS} = 10\text{V}$ $f = 1\text{MHz}$	-	285	-	pF
Output capacitance	C_{oss}		-	90	-	
Reverse transfer capacitance	C_{rss}		-	55	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 15\text{V}, V_{GS} = 4.5\text{V}$ $I_D = 1.7\text{A}$ $R_L = 8.8\Omega$ $R_G = 10\Omega$	-	8	-	ns
Rise time	t_r^{*5}		-	12	-	
Turn - off delay time	$t_{d(off)}^{*5}$		-	29	-	
Fall time	t_f^{*5}		-	13	-	

● **Gate Charge characteristics**($T_a = 25^\circ\text{C}$)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx 15\text{V}, I_D=3.5\text{A}$ $V_{GS} = 4.5\text{V}$	-	4.6	-	nC
Gate - Source charge	Q_{gs}^{*5}		-	0.7	-	
Gate - Drain charge	Q_{gd}^{*5}		-	1.5	-	

● **Body diode electrical characteristics** (Source-Drain)($T_a = 25^\circ\text{C}$)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_s^{*1}	$T_a = 25^\circ\text{C}$	-	-	1	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0\text{V}, I_s = 3.5\text{A}$	-	-	1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

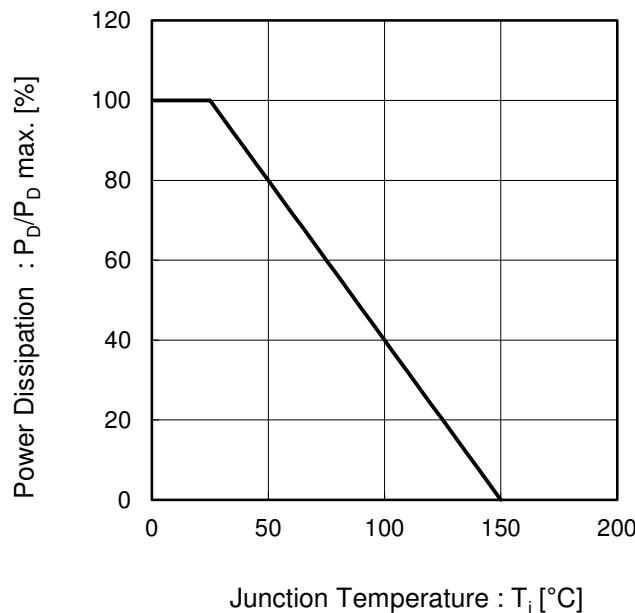


Fig.2 Maximum Safe Operating Area

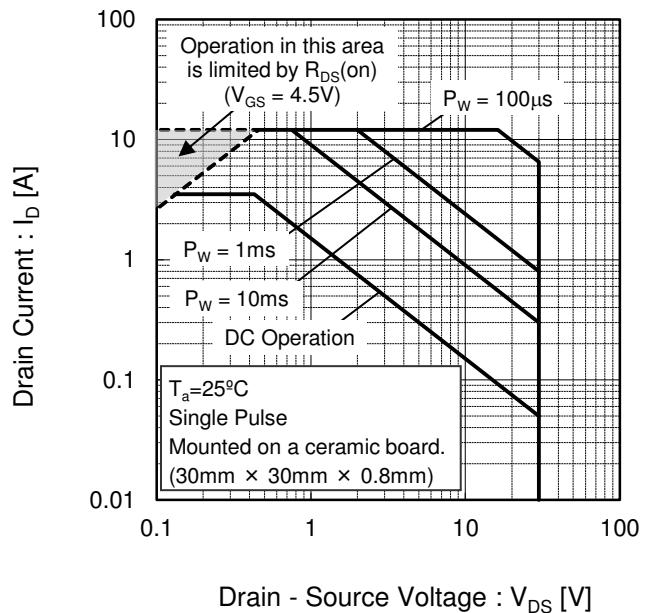


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

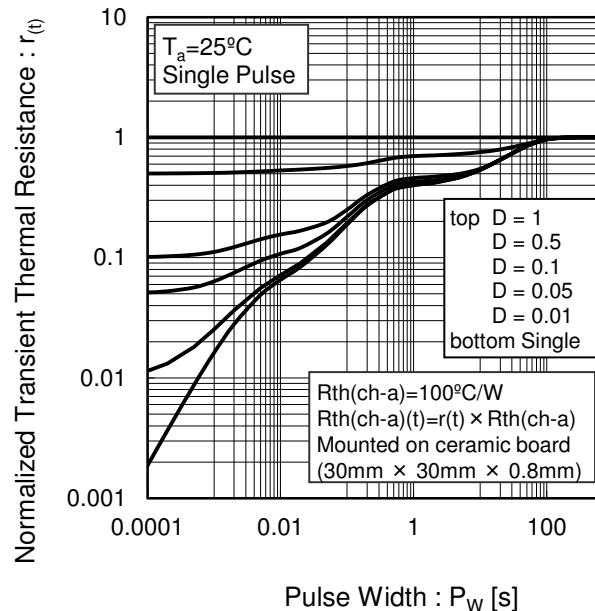
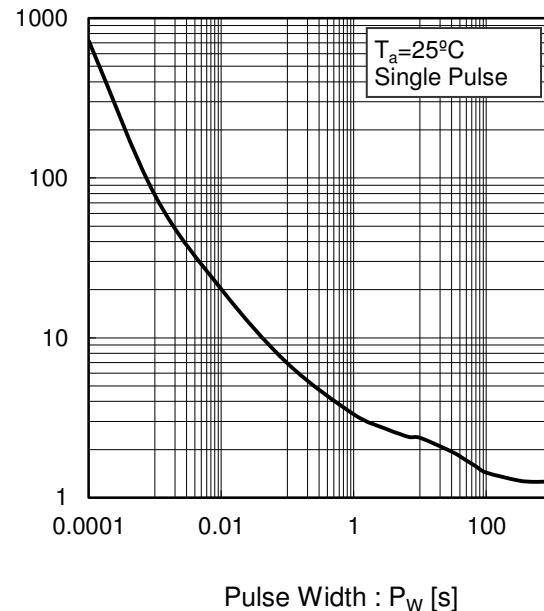


Fig.4 Single Pulse Maximum Power dissipation



● Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

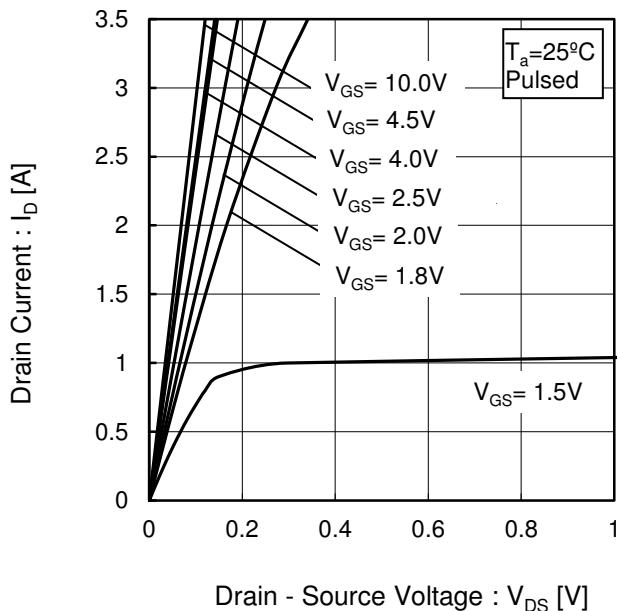


Fig.6 Typical Output Characteristics(II)

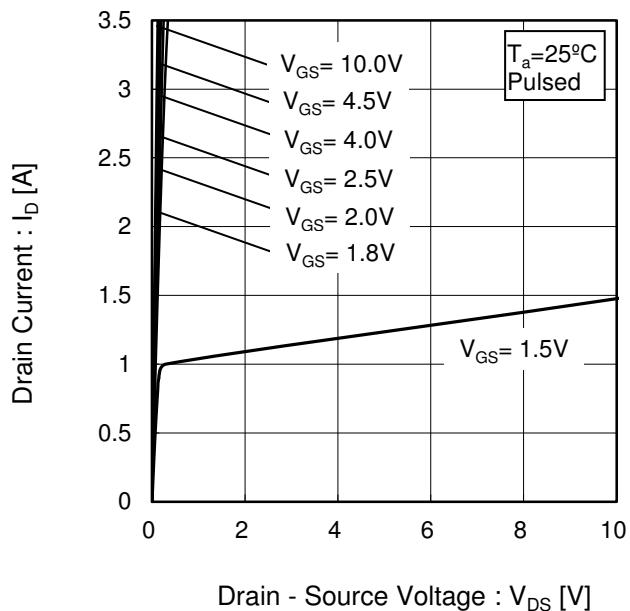


Fig.7 Breakdown Voltage
vs. Junction Temperature

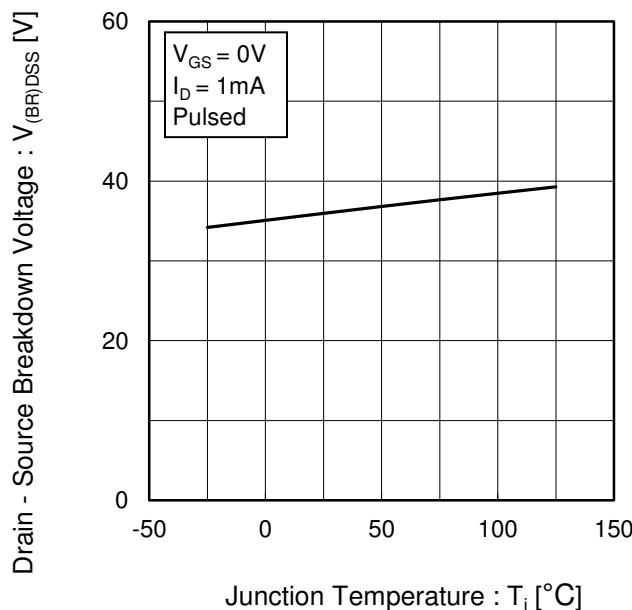
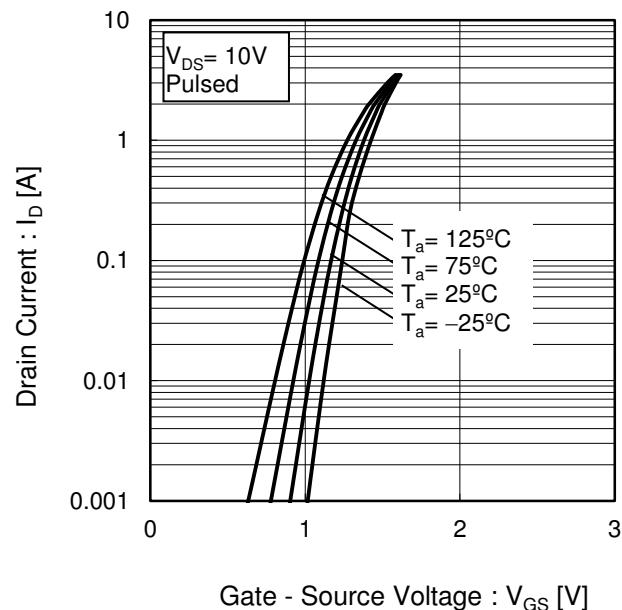


Fig.8 Typical Transfer Characteristics



● Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs. Junction Temperature

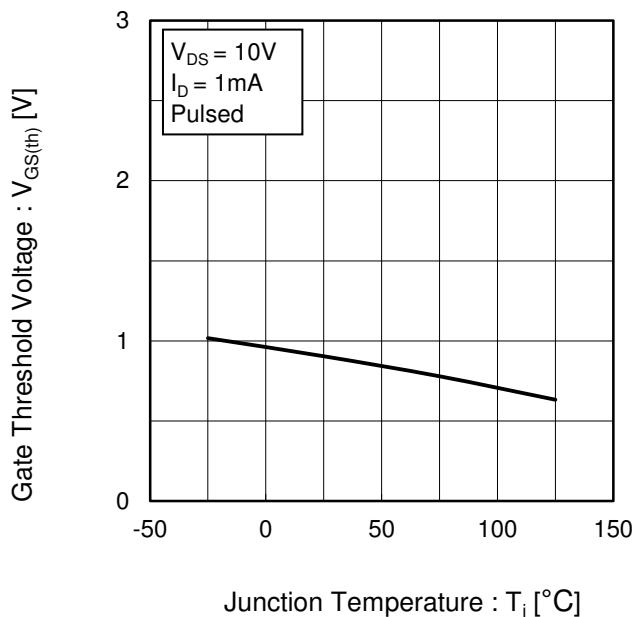


Fig.10 Transconductance vs. Drain Current

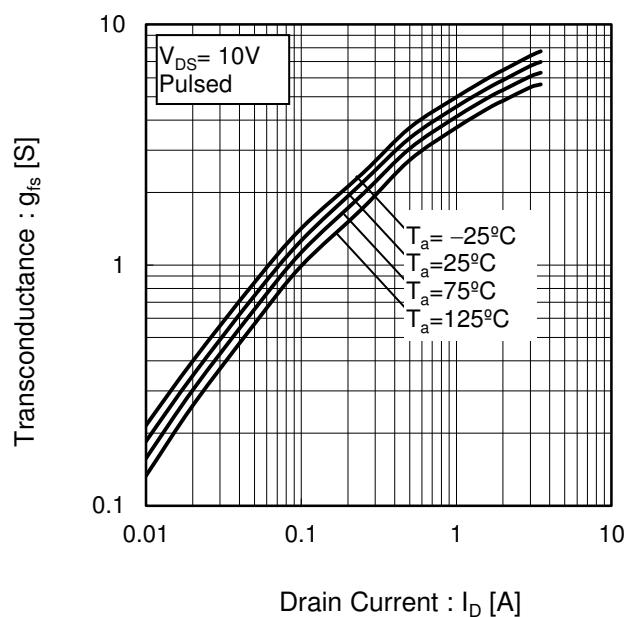


Fig.11 Drain Current Derating Curve

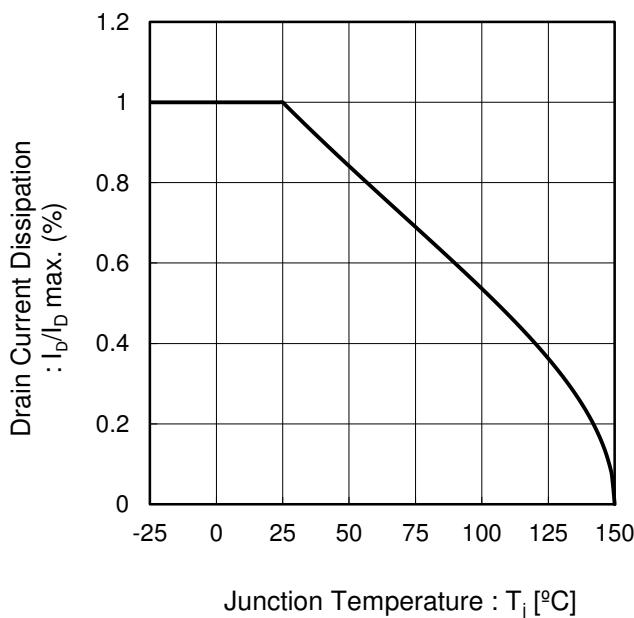
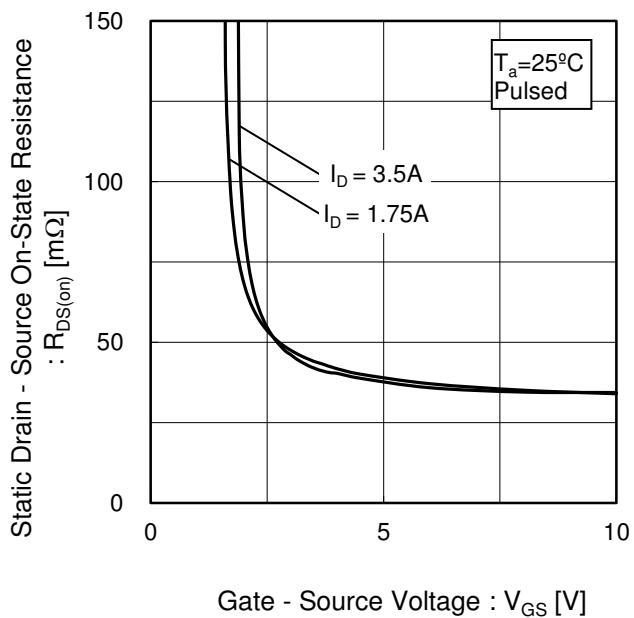


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



●Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I_D)

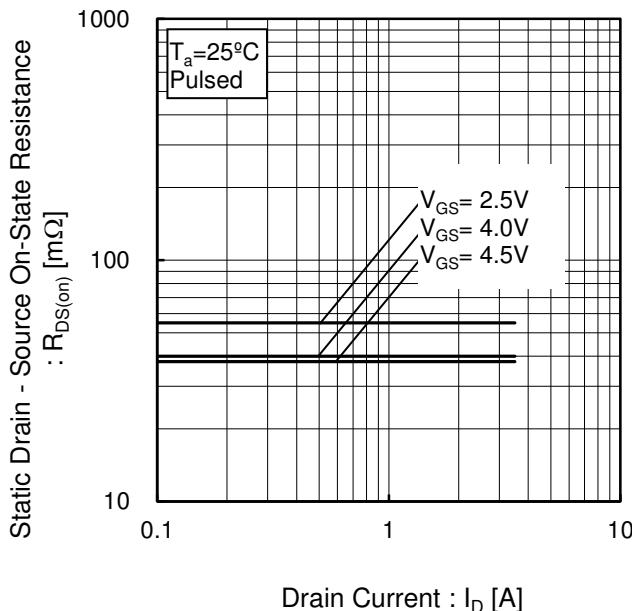


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature

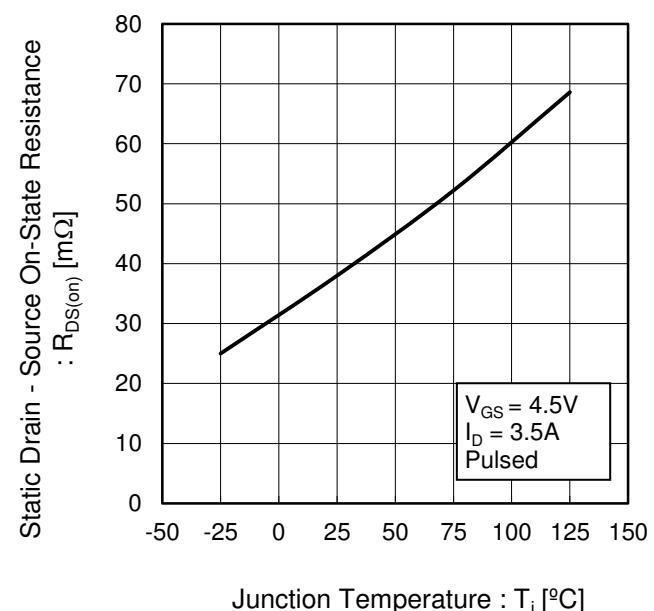


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

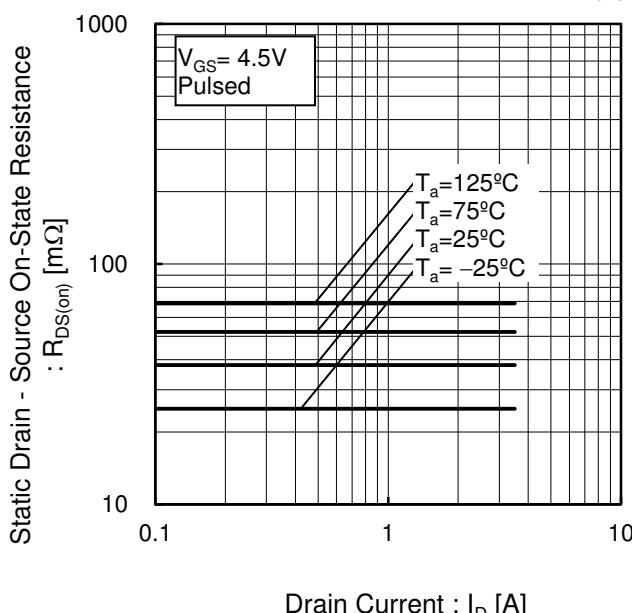
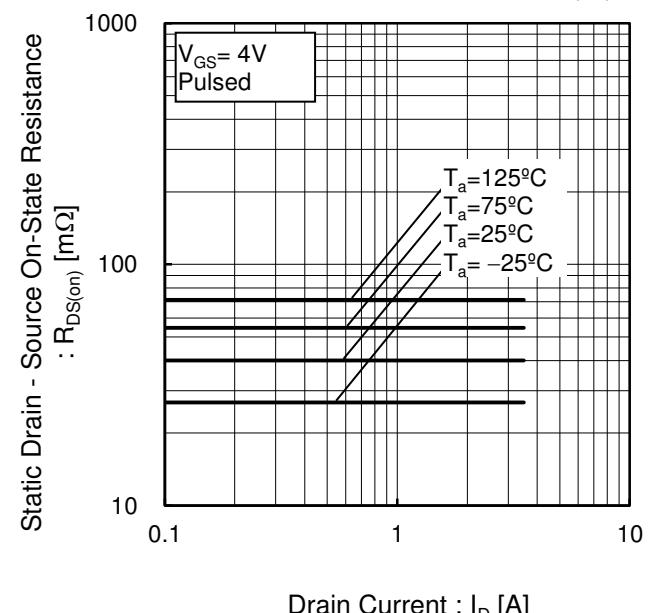


Fig.16 Static Drain-Source On-State Resistance vs. Drain Current(III)



●Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)

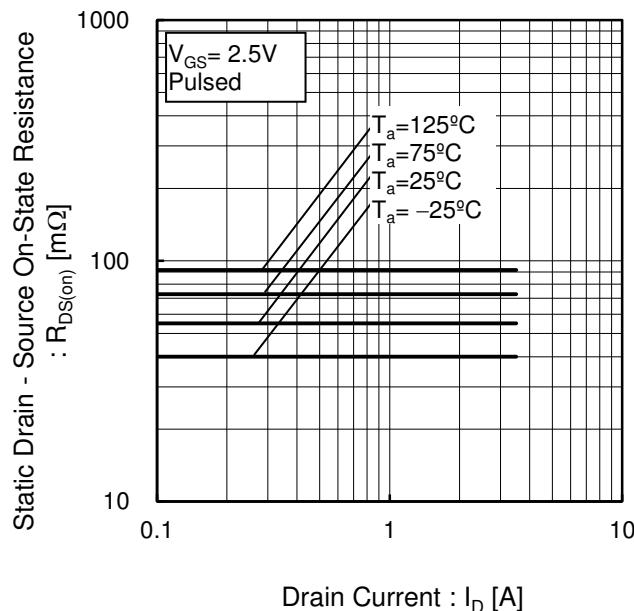


Fig.18 Typical Capacitance vs. Drain - Source Voltage

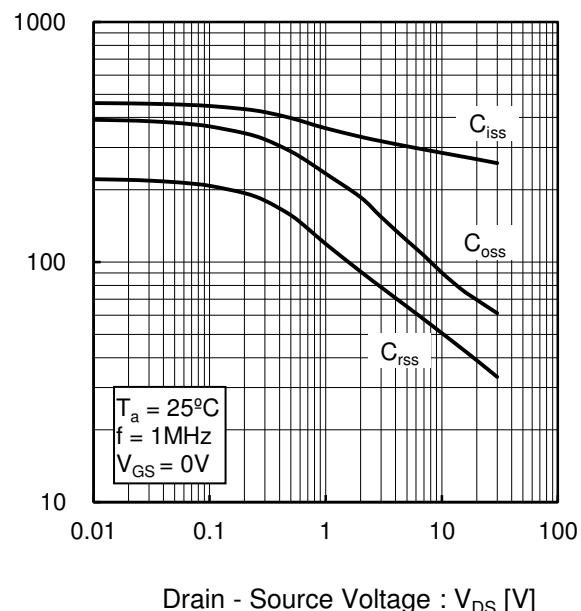


Fig.19 Switching Characteristics

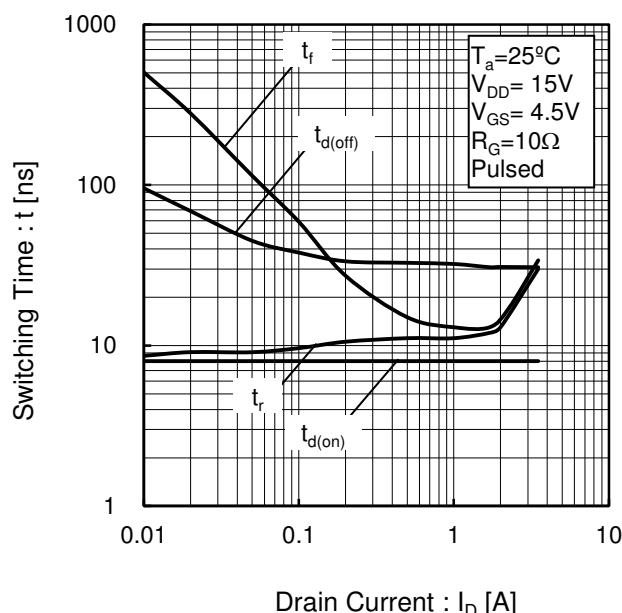
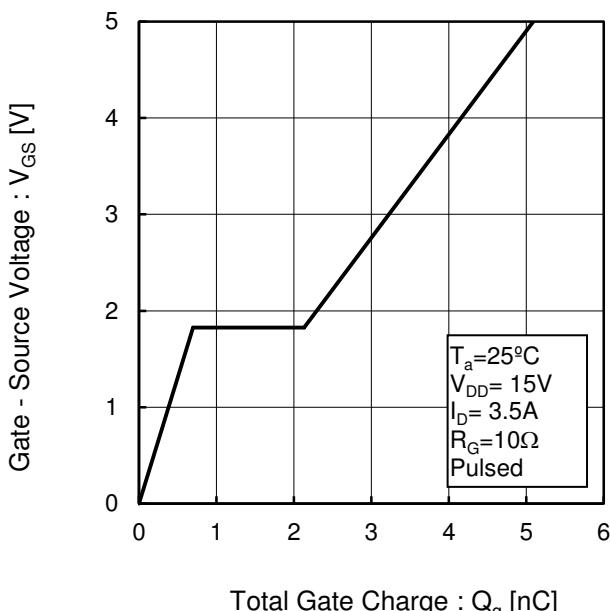
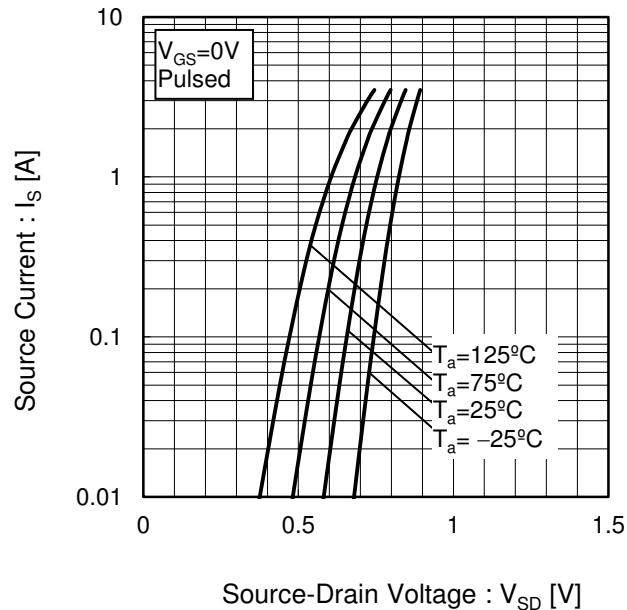


Fig.20 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.21 Source Current
vs. Source Drain Voltage



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

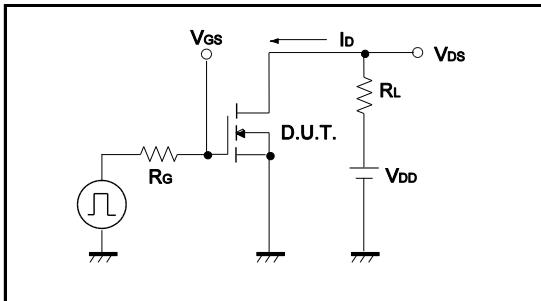


Fig.1-2 Switching Waveforms

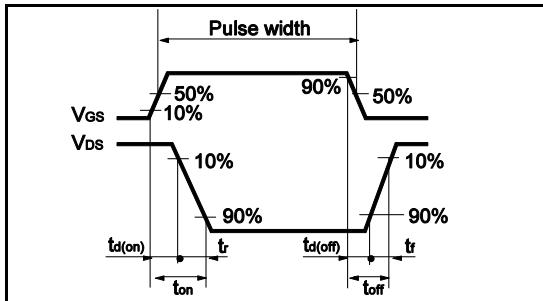


Fig.2-1 Gate Charge Measurement Circuit

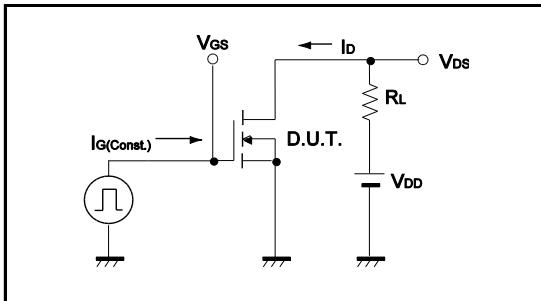
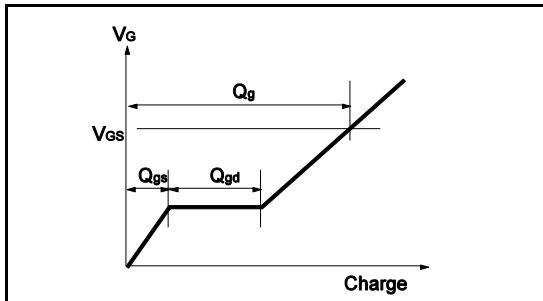
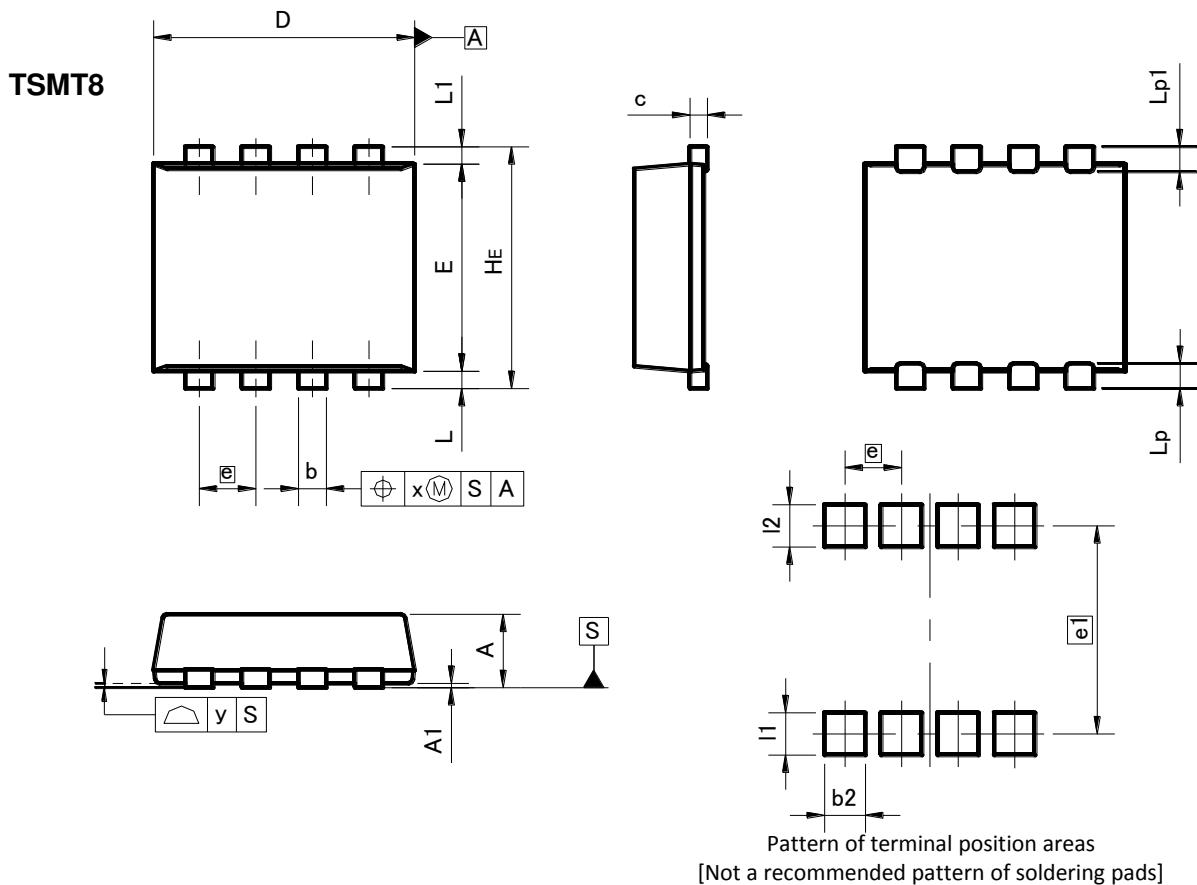


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.75	0.85	0.030	0.033
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
c	0.12	0.22	0.005	0.009
D	2.90	3.10	0.114	0.122
E	2.30	2.50	0.091	0.098
e	0.65		0.026	
HE	2.70	2.90	0.106	0.114
L	0.10	0.30	0.004	0.012
L1	0.10	0.30	0.004	0.012
Lp	0.19	0.39	0.007	0.015
Lp1	0.19	0.39	0.007	0.015
x	—	0.10	—	0.004
y	—	0.10	—	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	—	0.47	—	0.019
e1	2.41		0.095	
I1	—	0.49	—	0.019
I2	—	0.49	—	0.019

Dimension in mm / inches

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